- 2. (Original) The electronically tunable dielectric material of Claim 1, wherein the additional metal oxide phases comprise a total of from about 3 to about 65 weight percent of the material.
- 3. (Original) The electronically tunable dielectric material of Claim 1, wherein the additional metal oxide phases comprise a total of from about 5 to about 60 weight percent of the material.
- 4. (Original) The electronically tunable dielectric material of Claim 1, wherein the additional metal oxide phases comprise a total of from about 10 to about 50 weight percent of the material.
- 5. (Original) The electronically tunable dielectric material of Claim 1, wherein the dielectric material consists essentially of two of the additional metal oxide phases.
- 6. (Original) The electronically tunable dielectric material of Claim 5, wherein the two additional metal oxide phases have a weight ratio of from about 1:100 to about 100:1.
- 7. (Original) The electronically tunable dielectric material of Claim 5, wherein the two additional metal oxide phases have a weight ratio of from about 1:10 to about 10:1.
- 8. (Original) The electronically tunable dielectric material of Claim 5, wherein the two additional metal oxide phases have a weight ratio of from about 1:5 to about 5:1.

- 9. Cancel claim 9.
- 10. (Original) The electronically tunable dielectric material of Claim 1, wherein the at least one electronically tunable dielectric phase comprises barium strontium titanate.

'n

11. (Original) The electronically tunable dielectric material of Claim 10, wherein the barium strontium titanate is of the formula BaxSr1-xTiO3, where x is from about 0.15 to about 0.6.

12. Cancel claim 12.

- 13. (Original) The electronically tunable dielectric material of Claim 1, wherein the additional metal oxide phases comprise oxides of at least two metals selected from Mg, Si, Ca, Zr, Ti and Al.
- 14. (Original) The electronically tunable dielectric material of Claim 1, wherein the additional metal oxide phases comprise at least two Mg-containing compounds.
- 15. (Original) The electronically tunable dielectric material of Claim 14, further comprising at least one Mg-free compound.
- 16. (Original) The electronically tunable dielectric material of Claim 15, wherein the Mg-free compound comprises an oxide of a metal selected from Si, Ca, Zr, Ti and Al.

- 17. (Original) The electronically tunable dielectric material of Claim 15, wherein the Mg-free compound comprises a rare earth oxide.
- 18. (Original) The electronically tunable dielectric material of Claim 1, wherein the additional metal oxide phases comprise a Mg-containing compound and a Mg-free compound.
- 19. (Original) The electronically tunable dielectric material of Claim 18, wherein the Mg-free compound comprises an oxide of a metal selected from Ca, Si, Zr, Ti and Al.
- 20. (Original) The electronically tunable dielectric material of Claim 1, wherein the additional metal oxide phases comprise at least one material selected from Mg2SiO4, MgO, CaTiO3, MgZrSrTiO6, MgTiO3, MgAl2O4, WO3, SnTiO4, ZrTiO4, CaSiO3, CaSnO3, CaWO4, CaZrO3, MgTa2O6, MgZrO3, MnO2, PbO, Bi2O3 and La2O3.
- 21. (Original) The electronically tunable dielectric material of Claim 1, wherein the additional metal oxide phases comprise at least one material selected from Mg2SiO4, MgO, CaTiO3, MgZrSrTiO6, MgTiO3, MgAl2O4, MgTa2O6 and MgZrO3.
- 22. (Original) The electronically tunable dielectric material of Claim 1, wherein the material has a tunability of at least 25 percent at 8V/micron.
- 23. (Original) The electronically tunable dielectric material of Claim 1, wherein the AMENDMENT -- Page 6 of 12

material has a tunability of at least 30 percent at 8V/micron.